

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1 (canceled)

2. (currently amended) ~~The cleaning polish etch composition as recited in claim 1,~~  
A cleaning polish etch composition for treating a previously superfinished surface of a substrate by mechanically rubbing the previously superfinished surface of the substrate with a pad while contacting the previously superfinished surface of the substrate with the cleaning polish etch composition, wherein the substrate is selected from a group consisting of a glass disk substrate, a ceramic disk substrate, and a glass-ceramic disk substrate for use in a data storage device, the cleaning polish etch composition consisting essentially of:

a carrying fluid;

etchant for etching the previously superfinished surface of the substrate and/or attached slurry particles, wherein the cleaning polish etch composition is not a slurry.

3. (original) The cleaning polish etch composition as recited in claim 2, wherein the substrate is a silicate-based glass disk substrate.

4. (original) The cleaning polish etch composition as recited in claim 3, wherein the cleaning polish etch composition has a pH of approximately 0 to 4.

5. (original) The cleaning polish etch composition as recited in claim 4, wherein the cleaning polish etch composition has a pH of approximately 0.8 to 3.0.

6. (original) The cleaning polish etch composition as recited in claim 5, wherein the cleaning polish etch composition has a pH of approximately 1.0 to 2.0.

7. (currently amended) ~~The cleaning polish etch composition as recited in claim 1,~~  
A cleaning polish etch composition for treating a previously superfinished surface of a substrate by mechanically rubbing the previously superfinished surface of the substrate with a pad while contacting the previously superfinished surface of the substrate with the cleaning polish etch composition, wherein the substrate is a head wafer selected from a group consisting of Sendust and Permalloy, the cleaning polish etch composition consisting essentially of:

a carrying fluid;

etchant for etching the previously superfinished surface of the substrate and/or attached slurry particles, wherein the cleaning polish etch composition is not a slurry.

8. (original) The cleaning polish etch composition as recited in claim 7, wherein the substrate is a Sendust head wafer.

9. (original) The cleaning polish etch composition as recited in claim 8, wherein the cleaning polish etch composition has a pH of approximately 6 to 10.

10. (original) The cleaning polish etch composition as recited in claim 9, wherein the cleaning polish etch composition has a pH of approximately 9.5 to 10.

11. (original) The cleaning polish etch composition as recited in ~~claim 1~~ claim 2, wherein the etchant is an acid or base solution.

12. (original) The cleaning polish etch composition as recited in claim 3, wherein the etchant is a metal etchant selected from a group consisting of Ce, Zr, Ti, Fe, Sn, Al, Cr, Ni, Mn and Zn, and combinations thereof.

13. (original) The cleaning polish etch composition as recited in claim 12, wherein the metal etchant is Ce.

14. (original) The cleaning polish etch composition as recited in claim 8, wherein the etchant is a metal etchant selected from a group consisting of Ce, Zr, Ti, Fe, Sn, Al, Cr, Ni, Mn and Zn, and combinations thereof.

15. (original) The cleaning polish etch composition as recited in claim 14, wherein the metal etchant is Fe.

Claims 16-32 (canceled)

Claim 33 (new): A cleaning polish etch composition for treating a previously superfinished surface of a silicate-based glass disk substrate for use in a data storage device by mechanically rubbing the previously superfinished surface of the silicate-based glass disk substrate with a pad while contacting the previously superfinished surface of the silicate-based glass disk substrate with the cleaning polish etch composition, the cleaning polish etch composition consisting essentially of:

a carrying fluid;

a Ce metal etchant for etching the previously superfinished surface of the silicate-based glass disk substrate and/or attached slurry particles, wherein the cleaning polish etch composition has a pH of approximately 1.0 to 2.0 and wherein the cleaning polish etch composition is not a slurry.

Claim 34 (new): A cleaning polish etch composition for treating a previously superfinished surface of a Sendust head wafer substrate by mechanically rubbing the previously superfinished surface of the Sendust head wafer substrate with a pad while contacting the previously superfinished surface of the Sendust head wafer substrate with the cleaning polish etch composition, the cleaning polish etch composition consisting essentially of:

a carrying fluid;

a Fe metal etchant for etching the previously superfinished surface of the Sendust head wafer substrate and/or attached slurry particles, wherein the cleaning polish etch composition has a pH of approximately 9.5 to 10 and wherein the cleaning polish etch composition is not a slurry.